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10/810,309OIA INFORMATION DISCLOSURE CITATION
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AKASAKI, et al.Filing Date
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2811

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TL	5,122,845 (counterpart Japanese App. 2-229476)	06/16/92	MANABE, et al.			
TL	4,855,249 (counterpart Japanese App. 62-119196)	08/08/89	AKASAKI, et al.			
TL	6,566,218 (counterpart Japanese App. 2002-043223)	05/20/03	OTANI, et al.			

FOREIGN PATENT DOCUMENTS

EX	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
TL	4-321280	11/11/92	JAPAN			Abstract	
TL	62-119196 (counterpart U.S. Patent 4,855,249)	05/30/87	JAPAN			Abstract	
TL	2-229476 (counterpart U.S. Patent 5,122,845)	09/12/90	JAPAN			Abstract	
TL	2002-043223 (counterpart U.S. Patent 2002-043223)	02/08/02	JAPAN			Abstract	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

TL	SUDA, et al., "Heteroepitaxial Growth of Group-III Nitrides on Lattice-Matched Metal Boride ZrB ₂ (0001) by Molecular Beam Epitaxy – Department of Electronic Science and Engineering, Kyoto University – 13 th International Conference Crystal Growth, August, 2001, 02a-SB2-20
TL	YUKAWA, et al. – 62 nd Autumn Meeting, 2001; Japan Society of Applied Physics, 12-R-14
TL	Yohei YUKAWA, "Study on the crystal growth and properties of group-III nitride semiconductors on ZrB ₂ substrates by metalorganic vapor phase epitaxy" Department of Electronic Science and Engineering Graduate School of Meijo University

EXAMINER	DATE CONSIDERED	07/20/05
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.		